



# Reliability Report

## SGA/SGC Series in SOT-86 Package

### SnPb Plated

SGA-2186	SGA-3286	SGA-4186	SGA-5286	SGA-6286
SGA-2286	SGA-3386	SGA-4286	SGA-5386	SGA-6386
SGA-2386	SGA-3486	SGA-4386	SGA-5486	SGA-6486
SGA-2486	SGA-3586	SGA-4486	SGA-5586	
		SGA-4586		

### Matte Sn, RoHS Compliant

SGA-2186Z	SGA-3286Z	SGA-4186Z	SGA-5286Z	SGA-6286Z	SGC-2386Z
SGA-2286Z	SGA-3386Z	SGA-4286Z	SGA-5386Z	SGA-6386Z	SGC-2486Z
SGA-2386Z	SGA-3486Z	SGA-4386Z	SGA-5486Z	SGA-6486Z	SGC-4386Z
SGA-2486Z	SGA-3586Z	SGA-4486Z	SGA-5586Z		SGC-4486Z
		SGA-4586Z			SGC-6386Z



303 S. Technology Ct, Broomfield CO, 80021

Phone: (800) SMI-MMIC

<http://www.sirenza.com>

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# SGA/SGC in SOT-86 Reliability Report

## I. Overview

This reliability report describes the reliability test conditions and results for the SGA and SGC series of Transistors and Gain Blocks. The data is comprised of initial qualification tests and reliability monitoring tests. These tests include humidity (autoclave), extreme hot and cold environments (temperature cycling), moisture sensitivity (MSL-1 and solder reflow testing).

## II. Introduction

Sirenza Microdevices' SGA family are Silicon Germanium (SiGe) Gain Blocks that offer benefits not attainable with conventional silicon bipolar technologies. This family of products offer lower power consumption, high output power at high efficiency, high integration levels, at low cost.

Sirenza Microdevices SGC family of products are low cost, high performance SiGe HBT gain blocks. These Darlington designs contain a patented active bias network that provides stable current over temperature and process variations.

## III. Fabrication Technology

These amplifiers are manufactured using a Silicon Germanium Heterojunction Bipolar Transistor (HBT) technology. This self-aligned emitter, double poly HBT process has been in production by our foundry since 1998. The process has been successfully used for a wide range of RFIC products including GSM PAs, DECT front end transceivers, LNAs & VCOs. This process offers comparable performance to GaAs HBTs with the added advantages of mature and high producible Silicon wafer processing.

## IV. Package Type

These SGA/SGC products are packaged in a plastic encapsulated SOT-86 package that is assembled using a highly reproducible automated assembly process. The "Z" designates a lead-free lead frame using matte Tin plated leads and Green molding compound. The die is mounted using an industry standard thermally and electrically conductive silver epoxy.



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### V. Qualification Methodology

The Sirenza Microdevices qualification process consists of a series of tests designed to stress various potential failure mechanisms. This testing is performed to ensure that Sirenza Microdevices products are robust against potential failure modes that could arise from the various die and package failure mechanisms stressed. The qualification testing is based on JEDEC test methods common to the semiconductor industry. A FMEA approach is used to determine the test methods to be included in the qualification plan. The manufacturing test specifications are used as the PASS/FAIL criteria for initial and final DC/RF tests.

### VI. Qualification Family

The SGA/SGC products use the same IC technology, process and materials, as well as the assembly process and materials. All parts numbers listed on the cover page are categorized as on qualification family and are qualified by association when one family member successfully completes qualification.

### VII. Operational Life Testing

Sirenza Microdevices defines operational life testing as a DC biased elevated temperature test performed at the maximum operational junction temperature limit. For the SGA/SGC family, the maximum operational temperature limit is 150°C. The purpose of the operational life test is to statistically show that the product operated at its maximum operational ratings will be reliable by operating several hundred devices for a total time of 1000 hours. The results for this test are expressed in device hours that are calculated by multiplying the total number of devices passing the test by the number of hours tested.

### VIII. Moisture Sensitivity Level - MSL Level 1 Device

The SGA/SGC family of products have successfully completed 168 hours of moisture soak (85°C/85%RH), followed by three passes through a convection reflow oven at 270°C (Z versions), or at 235°C (non-Z versions). The successful completion of this test classifies the part as JESD 22-A113B Moisture Sensitivity Level 1 (MSL-1). MSL-1 indicates that no special dry pack requirements or time limits from opening of static bag to reflow exist for these products. MSL-1 is highest level of moisture resistance that a device can be classified according to the above mentioned standard.



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### IX. Electrostatic Discharge Classification

Sirenza Microdevices classifies Human Body Model (HBM) electrostatic discharge (ESD) according to the JESD22-A114 convention. All pin pair combinations were tested. Each pin pair is stressed at one static voltage level using 1 positive and 1 negative pulse polarity to determine the weakest pin pair combination. The weakest pin pair is tested with 3 devices below and above the failure voltage to classify the part. The Pass/Fail status of a part is determined by the manufacturing test specification. The ESD class quoted indicates that the device passed exposure to a certain voltage, but does not pass the next higher level. The following table indicates the JESD ESD sensitivity classification levels.

Class	Passes	Fails
0	0 V	<250 V
1A	250 V	500 V
1B	500 V	1000 V
1C	1000 V	2000 V
2	2000 V	4000 V

Part Number	ESD Rating
SGA-2186/2186Z	1A
SGA-2386/2386Z	0
SGA-2486/2486Z	0
SGA-3x86/3x86Z	0
SGA-4186/4186Z	1A
SGA-4286/4286Z	1A
SGA-4486/4486Z	1A
SGA-4586/4586Z	1A
SGA-5286/5286Z	1A
SGA-5486/5486Z	1B
SGA-6486/6486Z	1A
SGA-6586/6586Z	1A

### X. Operational Life Test Results

Date	Test Duration	Junction Temperature	Quantity	Device Hours
Q1-00	1000 hrs	125°C	398	398,000
Q3-00	1000 hrs	150°C	42	42,000
Q4-00	1000 hrs	150°C	60	60,000
Q2-02	1000 hrs	150°C	42	42,000
Q4-02	1000 hrs	150°C	42	42,000
Q3-03	1000 hrs	150°C	20	20,000
Q4-04	1000 hrs	150°C	40	40,000
Q4-04 (Z)	1000 hrs	150°C	80	80,000



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## XI. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
B	Preconditioning <sup>(1)</sup>	MSL1 Reflow @ 235°C Peak JESD22-A113C (Non-Z version)	1480	Pass
		MSL1 Reflow @ 270°C Peak JESD22-A113C (Z version)	305	Pass
B1a	Temperature Cycling	Air to Air, Soldered on PCB -65°C to 150°C 10 min dwell, 1 min transition 1000 cycles JESD22-A104B (Non-Z version)	13 <sup>(2)</sup>	Pass
		Air to Air, Soldered on PCB -65°C to 150°C 10 min dwell, 1 min transition 1000 cycles JESD22-A104B (Z version)	40	Pass
B3	Temperature Cycle	-65°C to +150°C 10 min dwell, 1 min transition 500 cycles JESD22-A104B (Non-Z version)	371	Pass
		-65°C to +150°C 10 min dwell, 1 min transition 1000 cycles JESD22-A104B (Z version)	30	Pass

(1) Preconditioning for Test Groups Bxx  
(2) 1 unit removed for bond defect (FA04173)



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## XI. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
B1b	High Temperature Operating Life	T <sub>j</sub> = 150°C <sup>(3)</sup> 1000 hours JESD22-A108B (Non-Z version)	644	Pass
		T <sub>j</sub> = 150°C 1000 hours JESD22-A108B (Z version)	80	Pass
B1c	HAST	T <sub>amb</sub> =110°C, 85%RH Biased, 264 hours JESD22-A110B (Non-Z version)	10	Pass
		T <sub>amb</sub> =110°C, 85%RH Biased, 264 hours JESD22-A110B (Z version)	25	Pass
B2	Autoclave	T <sub>amb</sub> =121°C, 100%RH Un-Biased, 96 hours JESD22-A102C (Non-Z version)	269	Pass
		T <sub>amb</sub> =121°C, 100%RH Un-Biased, 96 hours JESD22-A102C (Z version)	30	Pass

(3) 398 units were done at T<sub>j</sub>=125C



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## XI. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
B1d	Power Temperature Cycle	-40°C to +85°C Cycled bias (5' on/5'off) 1000 cycles JESD22-A109A (Non Z version)	10	Pass
		-40°C to +85°C Cycled bias (5' on/5'off) 1000 cycles JESD22-A109A (Z version)	30	Pass
C	Low Temperature Storage	Tamb=-40°C 1000 hours (Non Z version)	20	Pass
		Tamb=-40°C 1000 hours (Z version)	40	Pass
D	High Temperature Storage	Tamb=150°C 1000 hours JESD22-A103B (Non Z version)	218	Pass
		Tamb=150°C 1000 hours JESD22-A103B (Z version)	40	Pass



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### XI. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
F	Tin Whisker	Tamb=60°C, 90%RH 2600 hours	10	Pass
K	Solderability	Dip & Look Steam Age Condition C Dip Condition A, 215°C JESD22-B102C (Non-Z version)	59	Pass
		Dip & Look Steam Age Condition C Dip Condition A, 215°C JESD22-B102C (Z version)	15	Pass
		Dip & Look Steam Age Condition C Dip Condition B, 245°C JESD22-B102C (Z version)	15	Pass



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## XII. Junction Temperature Determination

One key issue in performing qualification testing is to accurately determine the junction temperature of the device. Sirenza Microdevices uses a 3um spot size emissivity corrected infrared camera measurement to resolve the surface temperature of the device at the maximum operational power dissipation. Results are displayed below for the SGA-6486 and SGA-6586Z.

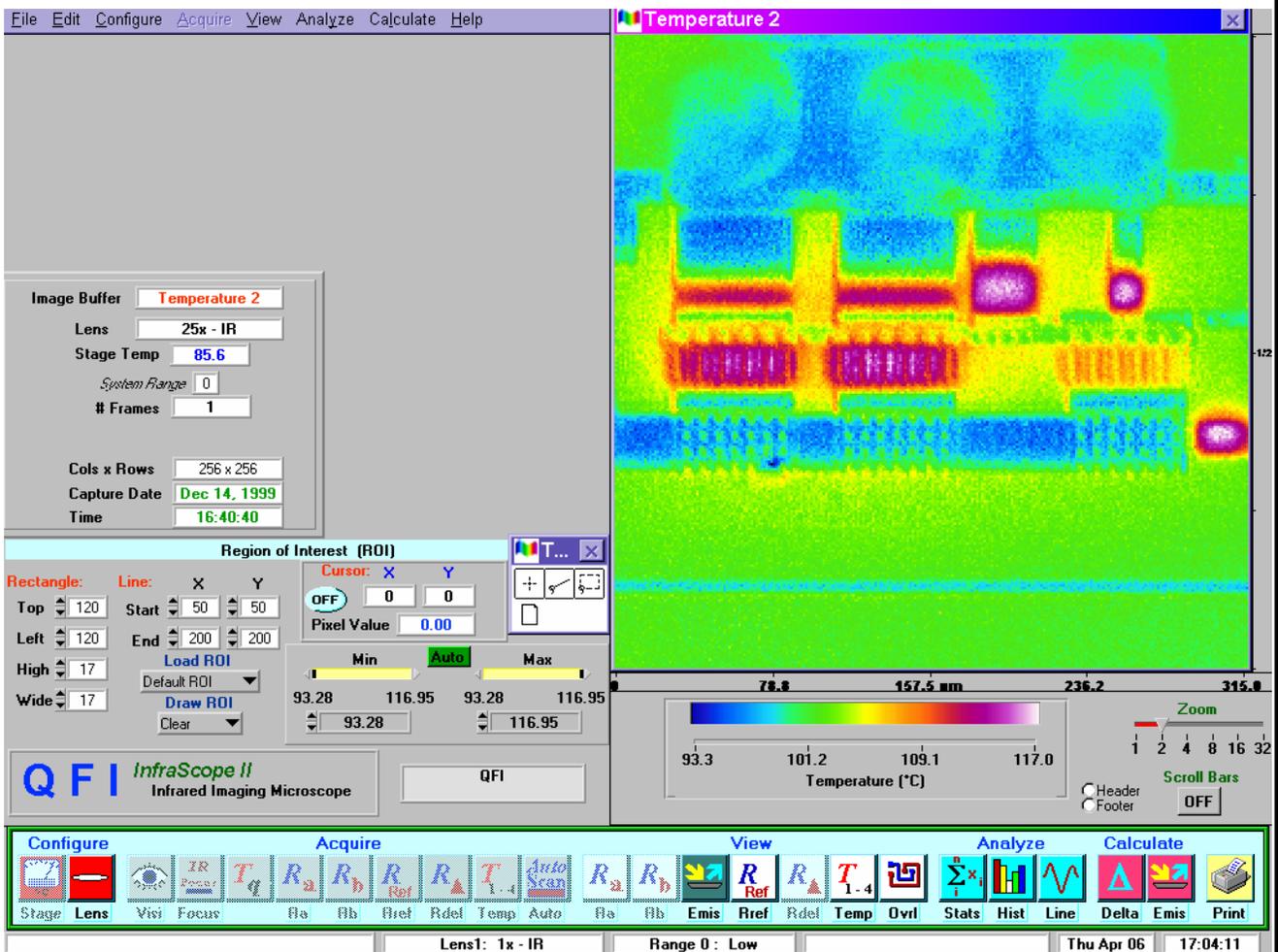


Figure 1: Infrared Thermal Image of SGA-6486,  $V_d = 4.65V$ ,  $I_d = 80.3mA$ ,  $T_{lead} = 85.5^{\circ}C$



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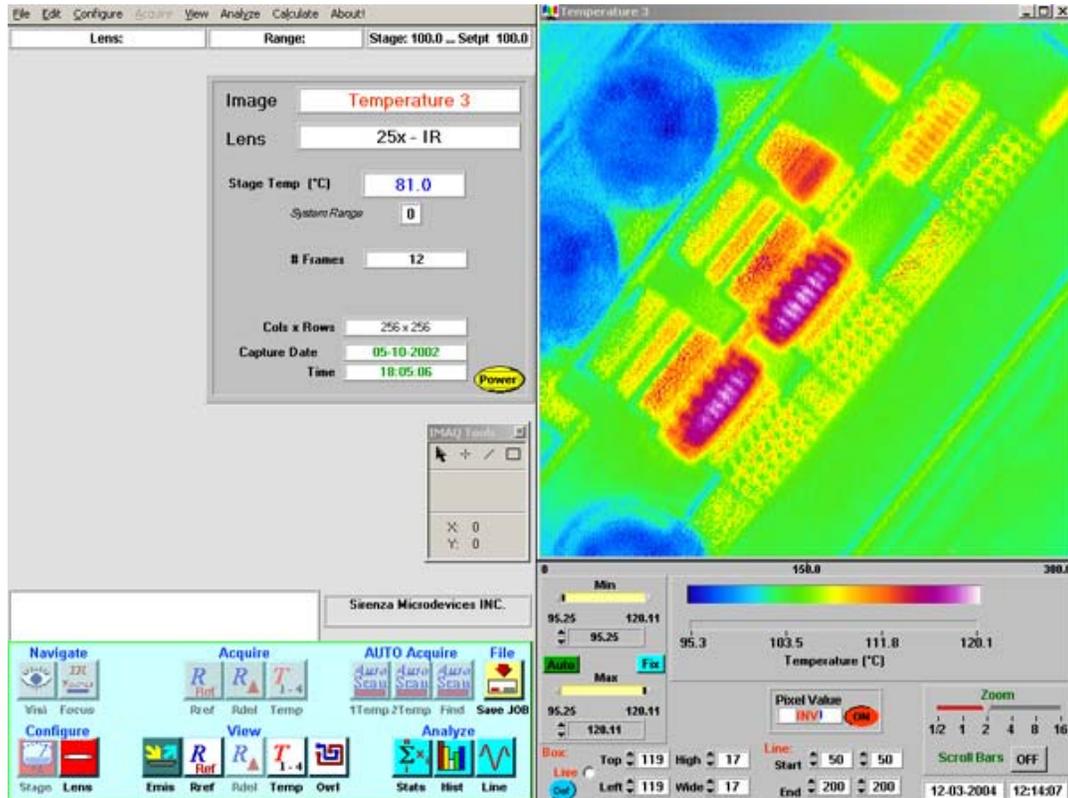


Figure 2: Infrared Thermal Image of SGA-6586Z,  $V_d = 4.50V$ ,  $I_d = 80.2mA$ ,  $T_{lead} = 84.5^{\circ}C$